

## **Digital Transistors (BRT)** $R1 = 100 \text{ k}\Omega$ , $R2 = \infty \text{ k}\Omega$

**NPN Transistors with Monolithic Bias Resistor Network** 

## **MUN2241, MMUN2241L, MUN5241, DTC115TE, DTC115TM3, NSBC115TF3**

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a baseemitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

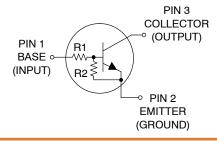
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS

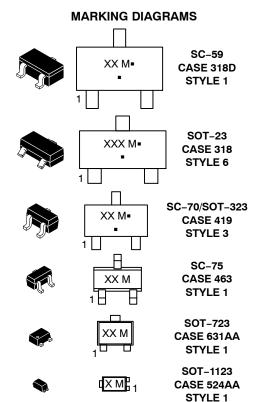
#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	6	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **PIN CONNECTIONS**





XXX = Specific Device Code = Date Code\* = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been DISCONTINUED. Please refer to the table on page 2.

1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2241T1G	8U	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2241LT1G	A8U	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5241T1G	AW	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC115TET1G	7V	SC-75 (Pb-Free)	3000 / Tape & Reel
DTC115TM3T5G	7D	SOT-723 (Pb-Free)	8000 / Tape & Reel

#### **DISCONTINUED** (Note 1)

NSBC115TF3T5G	P (90°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel
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<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>1.</sup> **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on <a href="https://www.onsemi.com">www.onsemi.com</a>.

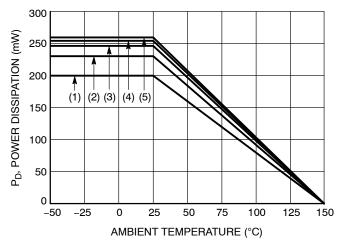


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

<sup>\*</sup>  $(\dot{x}\dot{x}^{\circ})$  = Degree rotation in the clockwise direction.

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTER	ISTICS (SC-59) (MUN2241)			
Total Device Dissipation		P <sub>D</sub>		
$T_A = 25^{\circ}C$	(Note 2)	_	230	mW
D	(Note 3)		338	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Derate above 25°C	(Note 2)		1.8 2.7	mW/°C
	(Note 3)		2.1	
Thermal Resistance,	(Note 2)	$R_{ hetaJA}$	540	°C/W
Junction to Ambient	(Note 3)		370	
Thermal Resistance,	(Note 2)	$R_{ hetaJL}$	264	°C/W
Junction to Lead	(Note 3)		287	
Junction and Storage Ten	perature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTER	ISTICS (SOT-23) (MMUN2241L)			
Total Device Dissipation		P <sub>D</sub>		
$T_A = 25^{\circ}C$	(Note 2)		246	mW
Devete above 05°C	(Note 3)		400	m\\\//°C
Derate above 25°C	(Note 2) (Note 3)		2.0 3.2	mW/°C
Thermal Resistance,	(Note 1)	$R_{ hetaJA}$	508	°C/W
Junction to Ambient	(Note 3)	I GJA	311	5,
Thermal Resistance,	(Note 2)	$R_{ hetaJL}$	174	°C/W
Junction to Lead	(Note 3)	· ·0JL	208	5,
Junction and Storage Ten	perature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTER	ISTICS (SC-70/SOT-323) (MUN5241)	J		
Total Device Dissipation		P <sub>D</sub>	I	
T <sub>A</sub> = 25°C	(Note 2)		202	mW
-A	(Note 3)		310	*****
Derate above 25°C	(Note 2)		1.6	mW/°C
	(Note 3)		2.5	
Thermal Resistance,	(Note 2)	$R_{ hetaJA}$	618	°C/W
Junction to Ambient	(Note 3)		403	
Thermal Resistance,	(Note 2)	$R_{ hetaJL}$	280	°C/W
Junction to Lead	(Note 3)		332	
Junction and Storage Ten	nperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
	ICTICS (SC 75) (DTC115TE)	•		
THERMAL CHARACTER	1311C3 (3C-73) (D1C1131E)			
Total Device Dissipation	151105 (50-75) (D101151E)	PD		
	(Note 2)	P <sub>D</sub>	200	mW
Total Device Dissipation T <sub>A</sub> = 25°C	(Note 2) (Note 3)	P <sub>D</sub>	300	
Total Device Dissipation	(Note 2) (Note 3) (Note 2)	P <sub>D</sub>	300 1.6	mW mW/°C
Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C	(Note 2) (Note 3) (Note 2) (Note 3)		300 1.6 2.4	mW/°C
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C  Thermal Resistance,	(Note 2) (Note 3) (Note 2) (Note 3)	P <sub>D</sub>	300 1.6 2.4 600	
Total Device Dissipation T <sub>A</sub> = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)	R <sub>θJA</sub>	300 1.6 2.4 600 400	mW/°C
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten	(Note 2) (Note 3) (Note 2) (Note 3)  (Note 2) (Note 3)  perature Range		300 1.6 2.4 600	mW/°C
Total Device Dissipation TA = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)	$R_{ heta JA}$ $T_J, T_{ ext{stg}}$	300 1.6 2.4 600 400	mW/°C
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER  Total Device Dissipation	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3) (Note 3)  Inperature Range	R <sub>θJA</sub>	300 1.6 2.4 600 400 -55 to +150	mW/°C °C/W °C
Total Device Dissipation TA = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)  (Note 3)  Inperature Range  ISTICS (SOT-723) (DTC115TM3)	$R_{ heta JA}$ $T_J, T_{ ext{stg}}$	300 1.6 2.4 600 400 -55 to +150	mW/°C
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER  Total Device Dissipation  T <sub>A</sub> = 25°C	(Note 2) (Note 3) (Note 2) (Note 3)  (Note 2) (Note 3)  (Note 3)  INDEPTATION (DTC115TM3)  (Note 2) (Note 3)	$R_{ heta JA}$ $T_J, T_{ ext{stg}}$	300 1.6 2.4 600 400 -55 to +150	mW/°C °C/W °C
Total Device Dissipation  T <sub>A</sub> = 25°C  Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER  Total Device Dissipation	(Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)  (Note 3)  Inperature Range  ISTICS (SOT-723) (DTC115TM3)	$R_{ heta JA}$ $T_J, T_{ ext{stg}}$	300 1.6 2.4 600 400 -55 to +150	mW/°C °C/W °C
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER  Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 2) (Note 3) (Note 2) (Note 3)  (Note 2) (Note 3)  (Note 3)  (Note 3)  (Note 2) (Note 3)  (Note 2) (Note 3) (Note 2) (Note 3) (Note 2) (Note 3)	R <sub>θ</sub> JA T <sub>J</sub> , T <sub>stg</sub>	300 1.6 2.4 600 400 -55 to +150 260 600 2.0 4.8	mW/°C  °C/W  °C  mW  mW/°C
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C  Thermal Resistance, Junction to Ambient  Junction and Storage Ten  THERMAL CHARACTER  Total Device Dissipation $T_A = 25^{\circ}C$	(Note 2) (Note 3) (Note 2) (Note 3)  (Note 2) (Note 3)  (Note 3)  INDEPTATION (DTC115TM3)  (Note 2) (Note 3) (Note 2)	$R_{ heta JA}$ $T_J, T_{ ext{stg}}$	300 1.6 2.4 600 400 -55 to +150 260 600 2.0	mW/°C °C/W °C

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERI	STICS (SOT-1123) (NSBC115TF3)			
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 4) (Note 5) (Note 4) (Note 5)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 4) (Note 5)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 4)	$R_{ heta JL}$	193	°C/W
Junction and Storage Tem	perature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

<sup>2.</sup> FR-4 @ Minimum Pad.

Table 3. ELECTRICAL CHARACTERISTICS ( $T_A = 25^{\circ}C$ , unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	_	500	nAdc
Emitter-Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	_	0.1	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \mu A, I_E = 0)$	V <sub>(BR)</sub> CBO	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 6) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	-	-	Vdc
ON CHARACTERISTICS			•		
DC Current Gain (Note 6) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	160	350	-	
Collector–Emitter Saturation Voltage (Note 6) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 5.0 mA)	V <sub>CE(sat)</sub>	-	_	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	$V_{i(off)}$	-	0.6	0.5	Vdc
Input Voltage (on) (V <sub>CE</sub> = 0.3 V, I <sub>C</sub> = 1.0 mA)	V <sub>i(on)</sub>	1.5	1.0	-	Vdc
Output Voltage (on) ( $V_{CC} = 5.0 \text{ V}, V_B = 5.0 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OL</sub>	-	_	0.2	Vdc
Output Voltage (off) ( $V_{CC} = 5.0 \text{ V}, V_B = 0.25 \text{ V}, R_L = 1.0 \text{ k}\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	-	-	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

<sup>3.</sup> FR-4 @ 1.0 x 1.0 Inch Pad.

<sup>4.</sup> FR-4 @ 100 mm², 1 oz. copper traces, still air.
5. FR-4 @ 500 mm², 1 oz. copper traces, still air.

#### **TYPICAL CHARACTERISTICS - NSBC115TF3**

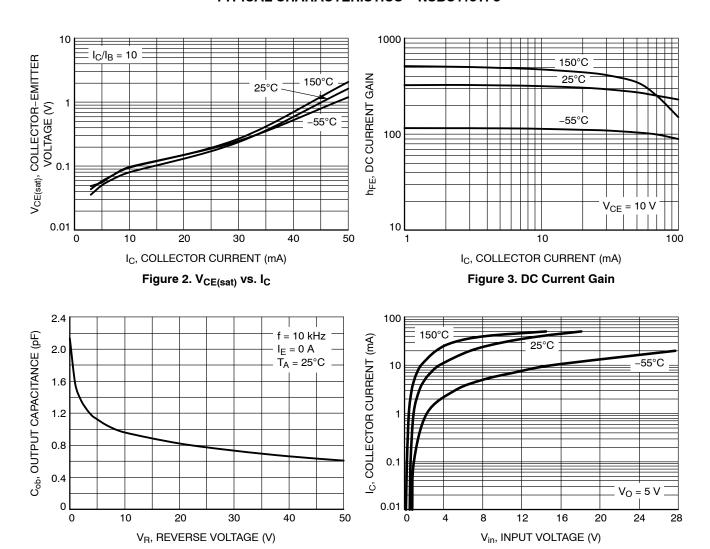


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

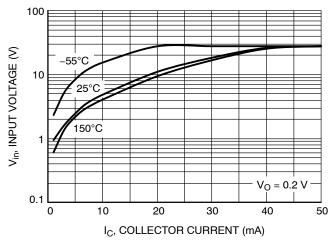


Figure 6. Input Voltage vs. Output Current

#### **PACKAGE DIMENSIONS**



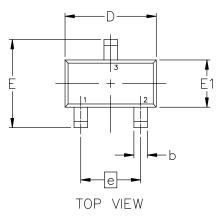
SC-59-3 2.90x1.50x1.15, 1.90P CASE 318D ISSUE J

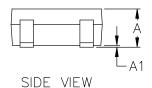
**DATE 15 FEB 2024** 

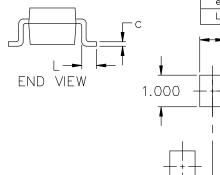
#### NOTES:

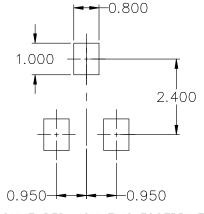
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- 2. ALL DIMENSION ARE IN MILLIMETERS.

	MILLIMETERS				
DIM	MIN.	NOM.	MAX.		
Α	1.00	1.15	1.30		
A1	0.01	0.06	0.10		
b	0.35	0.43	0.50		
С	0.09	0.14	0.18		
D	2.70	2.90	3.10		
E	2.50	2.80	3.00		
E1	1.30	1.50	1.70		
е	1.90 BSC				
L	0.20	0.40	0.60		









## RECOMMENDED MOUNTING FOOTPRINT\*

\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

# GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package\*

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

 STYLE 1:
 STYLE 2:
 STYLE 3:

 PIN 1. BASE
 PIN 1. ANODE
 PIN 1. ANODE

 2. EMITTER
 2. N.C.
 2. ANODE

 3. COLLECTOR
 3. CATHODE
 3. CATHODE

 STYLE 4:
 STYLE 5:
 STYLE 6:

 PIN 1. CATHODE
 PIN 1. CATHODE
 PIN 1. ANODE

 2. N.C.
 2. CATHODE
 2. CATHODE

 3. ANODE
 3. ANODE
 3. ANODE/CATHODE

**MILLIMETERS** 

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40

\_\_\_





#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

**DATE 14 AUG 2024** 

MAX

1.11

0.10

0.50

0.20

3.04

1.40

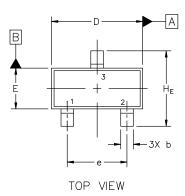
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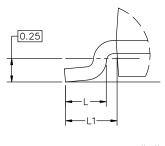
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0.69

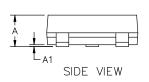
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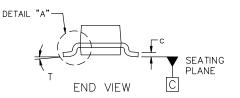
10°





DETAIL "A" Scale 3:1





## 2.90 3X 0.95 3X 0.56 -0.95 PITCH

#### NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

#### **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package



\* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

#### SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236) 2.90x1.3	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	







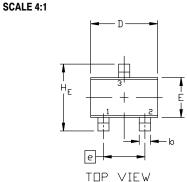
SC-70 (SOT-323) CASE 419 ISSUE R

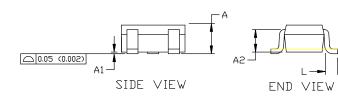
**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	M:	ILLIMETE	RS		INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





# GENERIC MARKING DIAGRAM

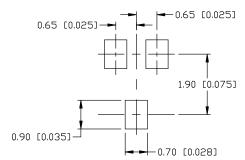


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1



#### SC75-3 1.60x0.80x0.80, 1.00P

**CASE 463 ISSUE H** 

**DATE 01 FEB 2024** 

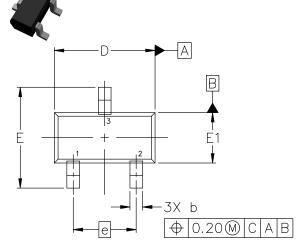
#### NOTES:

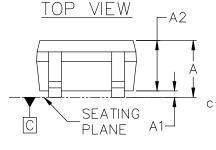
- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

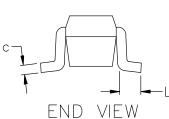
DIM	MILLIMETERS			
DIM	MIN.	NOM.	MAX.	
А	0.70	0.80	0.90	
A1	0.00	0.05	0.10	
A2	0.80 REF.			
b	0.15	0.20	0.30	
С	0.10	0.15	0.25	
D	1.55	1.60	1.65	
Е	1.50	1.60	1.70	
E1	0.70	0.80	0.90	
е	1.00 BSC			
L	0.10	0.15	0.20	

-0.356

0.787







SIDE VIEW

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3 CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3 CATHODE

SC75-3 1.60x0.80x0.80, 1.00P

RECOMMENDED MOUNTING FOOTPRINT\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES

1.803

0.508

REFERENCE MANUAL, SOLDERRM/D.

1.000

STYLE 4:	STYLE 5:
PIN 1. CATHODE	PIN 1. GATE
2. CATHODE	2. SOURCE
3. ANODE	3. DRAIN

**DESCRIPTION:** 

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PAGE 1 OF 1



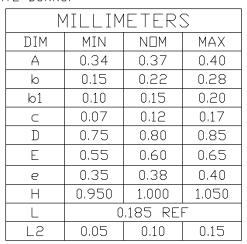


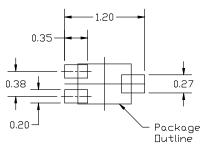
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3, MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



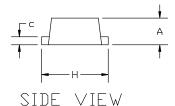


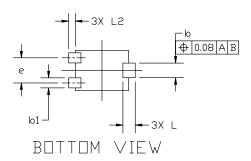
# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□LDERRM/D.

# D A B

TOP VIEW





# GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE
PIN 1. BASE	PIN
2. EMITTER	
<ol><li>COLLECTOR</li></ol>	:

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1



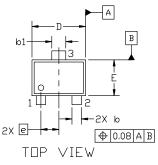


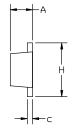
#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

**DATE 24 JAN 2024** 

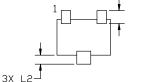
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



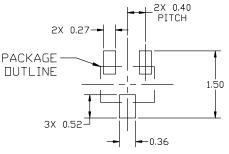






BOTTOM VIEW

#### MILLIMETERS DIM MIN. $N\square M$ . MAX. 0.45 0.50 0.55 Α 0.15 0.21 0.27 b b1 0.25 0.31 0.37 0.07 0.12 0.17 $\subset$ D 1.25 1.15 1.20 Ε 0.75 0.80 0.85 0.40 BSC е Н 1.20 1.25 1.15 0.29 REF L L2 0.15 0.20 0.25



## RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

## GENERIC MARKING DIAGRAM\*



XX = Specific Device Code M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	<ol><li>CATHODE</li></ol>	<ol><li>SOURCE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>DRAIN</li></ol>

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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